

Microcrystalline Silicon Solar Cells Deposited from SiF₄/H₂/Ar Gas Mixtures



Jean-Christophe DORNSTETTER^{(1),(2)}, Samir KASOUI⁽¹⁾, Erik JOHNSON⁽²⁾, and Pere ROCA I CABARROCAS⁽²⁾

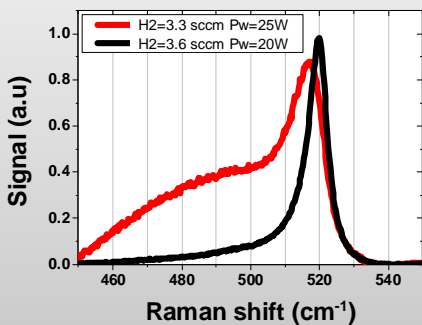
(1) TOTAL S.A. – Gas & Power, Tour Coupole – 2 place Jean Millier – La Défense 6, 92078 Paris La Défense, France
 (2) LPICM, CNRS, Ecole Polytechnique, 91128 Palaiseau Cedex, France

Introduction

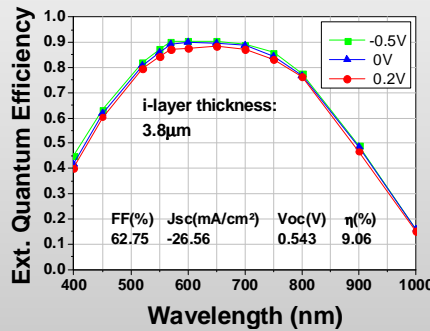
The fabrication of silicon simple PIN junction solar cells typically uses deposition plasmas made of SiH₄/H₂ for the microcrystalline silicon intrinsic layer. The deposition of such optimized layers requires a high H₂ dilution (SiH₄/H₂~0,04) and a crystalline fraction between 50% and 70%. The presence of at least 30% of amorphous fraction leads to the Light Induced Degradation (LID) phenomenon.

The (lab) world record is 10,9% [1] with advanced optimization of interfaces and of materials. Thickness of the i-layer is limiting: performance drops with too thick layers (>2,2µm). We propose [2] to use SiF₄/H₂/Ar plasma at high pressure with a high argon flux and a ratio of SiF₄/H₂~1. We aim for an understanding of the deposition process and an optimization of the material deposited from this plasma chemistry.

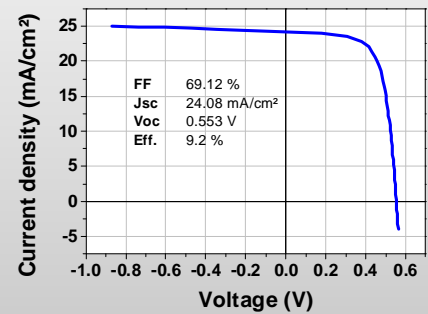
Cells Properties



- X_c controlled by H₂ flow and Power
- Layer fully crystallized
- No LID
- Correlation length ~5nm (FWHM @ 520)

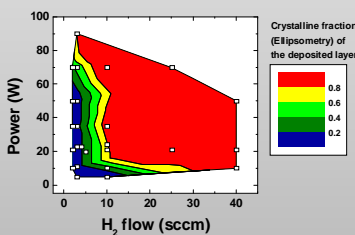
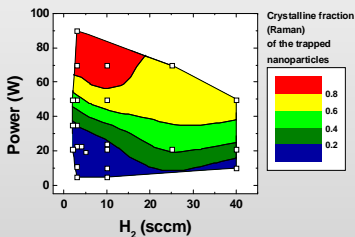


- Good collection properties
- Thick layer of 3.8µm
- Even for λ>800nm
- Forward/Reverse ratio >95%



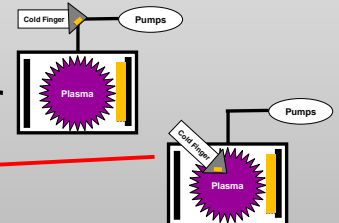
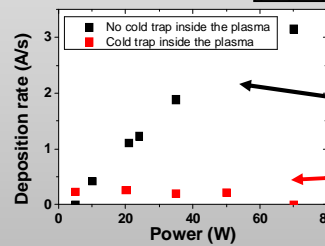
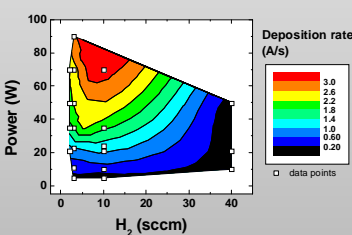
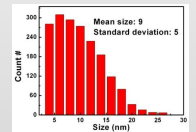
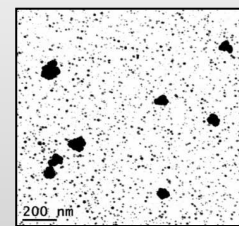
- Efficiency of 9.2% achieved
- V_{oc}>535mV (EPFL-IMT [1]) with X_c~1 !
- No sophisticated optimization
- Vacuum break between each layer

Growth Mechanism



Growth hypothesis: nanocrystal precursors:

- Powder trapping by cold finger (thermophoresis)
- Crystalline fraction study (powder/layer)
- Deposition rate deduced from ellipsometry
- Visualization of nanocrystals by TEM imaging



Prospects

- Cell fabrication transferred to Cluster-PECVD (depositions without vacuum break)
 - Optimization: plasma parameters, layer thicknesses, texturing...
 - Study for a deeper understanding of role of nanocrystals (use of mass spectrometer for instance)
 - Evaluation of gas consumption and increase of deposition rate
- Goal: exceed 10% efficiency

[1] Hanni *et al.*, IEEE Journal of Photovoltaics, DOI 10.1109/JPHOTOV.2012.2214766

[2] Dornstetter *et al.*, IEEE Journal of Photovoltaics, DOI 10.1109/JPHOTOV.2012.2221683